

2N499
GERMANIUM
MICRO ALLOY
DIFFUSED-BASE
TRANSISTOR
PNP POLARITY

I. General Description

This transistor is a PNP, germanium, triode transistor designed primarily for low power IF and RF amplifier applications in the up to 100mc frequency range for industrial service.

II. Mechanical Data

A. Outline drawing TO-1

B. Terminal Designations

<u>Terminal</u>	<u>Element</u>
1	Emitter
2	Base
3	Collector
Case	All leads insulated from case

III. Absolute Maximum Ratings

A. Maximum Temperature

1. Storage Temperature -65°C to +100°C
2. Lead Temperature, 1/16" $\pm$ 1/32" from case
for 10 seconds 230°C

B. Maximum Reverse Rating (T = 25°C)

1. Emitter-base, V_{EBO} -0.5 volt
2. Collector-base, V_{CBO} - 30 volts
3. Collector-emitter, V_{CEO} - 18 volts

C. Maximum Current (DC)

1. Collector Current, I_C - 50 ma

D. Power

1. Maximum Power Dissipation (T = 25°C) 60 mw
2. Derating Factor above 25°C 0.8 mw/°C